SHANGHAI SUNRISE ELECTRONICS CO., LTD.

2CK120

SILICON EPITAXIAL
PLANAR SWITCHING DIODE

REVERSE VOLTAGE: 75V
FORWARD CURRENT: 150mA

TECHNICAL SPECIFICATION

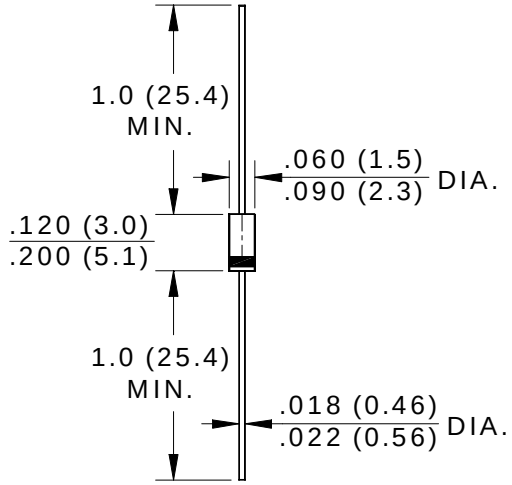
FEATURES

- Small glass structure ensures high reliability
- Fast switching
- Low leakage
- High temperature soldering guaranteed:
  250°C/10S/9.5mm lead length
  at 5 lbs tension

MECHANICAL DATA

- Terminal: Plated axial leads solderable per MIL-STD 202E, method 208C
- Case: Glass,hermetically sealed
- Polarity: Color band denotes cathode
- Mounting position: Any

DO - 35



Dimensions in inches and (millimeters)

MAXIMUM RATINGS AND CHARACTERISTICS

(Ratings at 25°C ambient temperature unless otherwise specified)

RATINGS	SYMBOL	VALUE	UNITS
Reverse Voltage	V_R	75	V
Peak Reverse Voltage	V_{RM}	100	V
Forward Current (average)	I_O	150	mA
Repetitive Forward Peak Current	I_{FRM}	400	mA
Forward Voltage (I_F=10mA)	V_F	1	V
Reverse Current (V_R=20V)	I_{R1}	25	nA
Reverse Current (V_R=75V)		5	μA
Reverse Current (V_R=20V,T_J=100°C)	I_{R2}	50	μA
Capacitance (note 1)	Ct	4	pF
Reverse Charge (I_F=10mA)	Qr	57	pC
Thermal Resistance (junction to ambient, note 2)	R_θ(ja)	0.35	°C/mW
Operating Junction and Storage Temperature Range	T_{STG},T_J	-55～+175	°C

Notes:

1. V_R=0V, f=1 MHz
2. Valid provided that leads are kept at ambient temperature at a distance of 8mm from case.